

Amendments to the claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-8 cancelled

9. (original) A method of manufacturing a semiconductor device comprising the steps of:

forming an electrode pad to come in contact with a surface of a semiconductor substrate provided with a desirable element region or a wiring layer provided on the surface of the semiconductor substrate;

forming an intermediate layer on a surface of the electrode pad;

forming a pad layer to be a bonding pad on a surface of the intermediate layer and patterning the intermediate layer and the pad layer; and

forming a resin insulating film to cover edges of patterns of the bonding pad and the intermediate layer.

10. (original) The method of manufacturing a semiconductor device according to claim 9, wherein the step of forming a resin insulating film includes a step of applying a polyimide resin film.

11. (currently amended) The method of manufacturing a semiconductor device according to claim 9 ~~or 10~~, wherein the step of forming an intermediate layer includes a step of forming a titanium tungsten (TiW) layer by a sputtering method.

12. (original) The method of manufacturing a semiconductor device according to claim 11, wherein the step of forming a pad layer includes a step of forming a metal layer by sputtering.